

# Dedong Han

## List of Publications by Year in descending order

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papers

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41  
times ranked

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#	ARTICLE	IF	CITATIONS
1	Investigation on Transparent, Conductive ZnO:Al Films Deposited by Atomic Layer Deposition Process. <i>Nanomaterials</i> , 2022, 12, 172.	4.1	11
2	Structural Engineering Effects on Hump Characteristics of ZnO/InSnO Heterojunction Thin-Film Transistors. <i>Nanomaterials</i> , 2022, 12, 1167.	4.1	2
3	Back-End-of-Line Compatible InSnO/ZnO Heterojunction Thin-Film Transistors With High Mobility and Excellent Stability. <i>IEEE Electron Device Letters</i> , 2022, 43, 1251-1254.	3.9	3
4	High-Performance ZnO Thin-Film Transistors on Flexible PET Substrates With a Maximum Process Temperature of 100 Å°C. <i>IEEE Journal of the Electron Devices Society</i> , 2021, 9, 10-13.	2.1	10
5	Atomic Layer Deposition Deposited Al-Doped ZnO Films for Transistor Application. , 2021, , .		0
6	High-performance ZnO Thin-Film Transistors Prepared by Atomic Layer Deposition at Low Temperature. , 2021, , .		1
7	8.2: High Performance Oxide Thin Film Transistors Fabricated by Atomic Layer Deposition Process. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 141-141.	0.3	0
8	Pâ€1.7: Atomicâ€Layerâ€Deposition Deposited Superlatticeâ€Structure Alâ€Znâ€O Films for Thin Film Transistors Application. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 696-698.	0.3	0
9	36.3: Flexible ZnO Thinâ€Film Transistors Fabricated on PEN Substrate by Atomic Layer Deposition at Low Temperature. <i>Digest of Technical Papers SID International Symposium</i> , 2021, 52, 472-476.	0.3	1
10	Effects of Channel Thickness on Electrical Performance and Stability of High-Performance InSnO Thin-Film Transistors. <i>Membranes</i> , 2021, 11, 929.	3.0	15
11	Enhanced Performance of Atomic Layer Deposited Thin-Film Transistors With High-Quality ZnO/Al<sub>2</sub>O<sub>3</sub> Interface. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 518-523.	3.0	20
12	The Effects of Post Annealing Process on the Electrical Performance and Stability of Al-Zn-O Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2020, 41, 569-572.	3.9	16
13	High-Performance ZnO Thin-Film Transistors Prepared by Atomic Layer Deposition. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 2965-2970.	3.0	25
14	Performance Enhancement of TiZO Thin Film Transistors by Introducing a Thin ITO Interlayer. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 1302-1305.	2.1	1
15	Improving Performance of Tin-Doped-Zinc-Oxide Thin-Film Transistors by Optimizing Channel Structure. <i>Scientific Reports</i> , 2019, 9, 17175.	3.3	9
16	High-performance Al-Zn-O Thin-Film Transistors Sputtering at Different Power. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 4774-4777.	3.0	8
17	Enhanced electrical properties of dual-layer channel ZnO thin film transistors prepared by atomic layer deposition. <i>Applied Surface Science</i> , 2018, 439, 632-637.	6.1	24
18	Investigation of c-axis-aligned crystalline gadolinium doped aluminum-zinc-oxide films sputtered at room-temperature. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	6

#	ARTICLE	IF	CITATIONS
19	Enhancement Of Positive Bias Stress Stability For IGZO TFTs By A CAAC Gd-AZO Bulk Layer. , 2018, , .		0
20	Pâ€1.13: Influence of the Source/Drain Material on Oxide Semiconductor Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2018, 49, 557-560.	0.3	1
21	Titanium doped zinc oxide thin film transistors fabricated by cosputtering technique. Applied Surface Science, 2018, 459, 345-348.	6.1	15
22	High-Performance Ti-Doped Zinc Oxide TFTs With Double-Layer Gate Dielectric Fabricated at Low Temperature. IEEE Electron Device Letters, 2017, 38, 207-209.	3.9	12
23	Effects of Channel Layer Thickness on Characteristics of Flexible Nickel-Doped Zinc Oxide Thin-Film Transistors. IEEE Transactions on Electron Devices, 2017, 64, 1997-2000.	3.0	9
24	Oxygen Adsorption Effect of Amorphous InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2017, 38, 465-468.	3.9	14
25	AZO Thin Film Transistor Performance Enhancement by Capping an Aluminum Layer. IEEE Transactions on Electron Devices, 2017, 64, 2228-2232.	3.0	6
26	Bi-layer Channel AZO/ZnO Thin Film Transistors Fabricated by Atomic Layer Deposition Technique. Nanoscale Research Letters, 2017, 12, 223.	5.7	13
27	Oxygen Interstitial Creation in a-IGZO Thin-Film Transistors Under Positive Gate-Bias Stress. IEEE Electron Device Letters, 2017, 38, 1252-1255.	3.9	41
28	Fully transparent high performance thin film transistors with bilayer ITO/Al-Sn-Zn-O channel structures fabricated on glass substrate. Scientific Reports, 2017, 7, 1497.	3.3	20
29	High-Performance Flexible Tin-Zinc-Oxide Thin-Film Transistors Fabricated on Plastic Substrates. IEEE Transactions on Electron Devices, 2016, , 1-4.	3.0	11
30	Highâ€performance fully transparent Alâ€Snâ€Znâ€O thinâ€film transistors using doubleâ€channel structures. Electronics Letters, 2016, 52, 1069-1070.	1.0	4
31	Snâ€doped ZnO thinâ€film transistors with AZO, TZO and Al heterojunction source/drain contacts. Electronics Letters, 2016, 52, 302-304.	1.0	4
32	Effects of substrate temperature on performance of calciumâ€doped zinc oxide TFTs. Electronics Letters, 2015, 51, 1286-1288.	1.0	3
33	Paper No P20: Effects of the Channel Thickness on Characteristics of Ga-Doped Zinc Oxide Thin-Film Transistors Fabricated on Glass. Digest of Technical Papers SID International Symposium, 2015, 46, 87-87.	0.3	0
34	Performance enhancement of fully transparent tinâ€doped zinc oxide thinâ€film transistors fabricated by sputtering at low temperature. Electronics Letters, 2015, 51, 272-274.	1.0	1
35	High Performance Ti-Doped ZnO TFTs With AZO/TZO Heterojunction S/D Contacts. Journal of Display Technology, 2015, 11, 412-416.	1.2	12
36	Transparent gallium doped zinc oxide thin-film transistors fabricated on glass substrate. Thin Solid Films, 2015, 594, 266-269.	1.8	4

#	ARTICLE	IF	CITATIONS
37	High mobility transparent flexible nickel-doped zinc oxide thin-film transistors with small subthreshold swing. Electronics Letters, 2015, 51, 1595-1596.	1.0	4
38	Fully transparent flexible dual-layer channel Ga-doped ZnO thin-film transistors on plastic substrates. Electronics Letters, 2015, 51, 1069-1071.	1.0	3
39	High-performance full transparent tin-doped zinc oxide thin-film transistors fabricated on glass at low temperatures. Electronics Letters, 2014, 50, 1463-1465.	1.0	3
40	High-performance dual-layer channel ITO/TZO TFTs fabricated on glass substrate. Electronics Letters, 2014, 50, 633-635.	1.0	4
41	High-Performance Transparent AZO TFTs Fabricated on Glass Substrate. IEEE Transactions on Electron Devices, 2013, 60, 2432-2435.	3.0	52